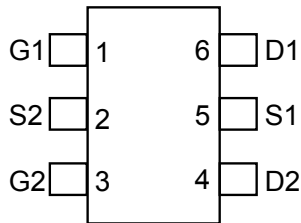


**Description**

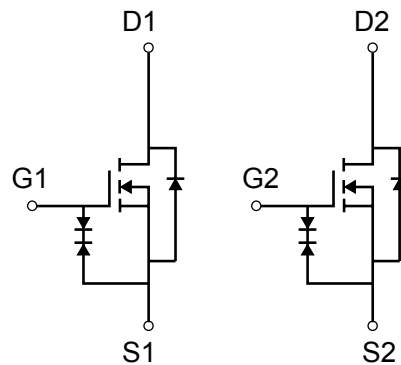
The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

MOSFET Product Summary		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (mΩ)	I <sub>D</sub> (A)
20	45@ VGS=4.5V	2

Top View(SOT23-6)



Internal Structure



**Absolute maximum rating@25°C**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±8	V
Continuous Drain Current <sup>(Note 1)</sup>	I <sub>D</sub>	T <sub>A</sub> =25°C	4.5
		T <sub>A</sub> =70°C	3.5
Pulsed Drain Current <sup>(Note 1)</sup>	I <sub>DM</sub>	18	A
Diode Continuous Forward Current <sup>(Note 1)</sup>	I <sub>S</sub>	1	A
Maximum Power Dissipation <sup>(Note 1)</sup>	P <sub>D</sub>	T <sub>A</sub> =25°C	1.4
		T <sub>A</sub> =70°C	0.89
Maximum Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to 150	
Thermal Characteristics			
Parameter	Symbol	Maximum	Units
Thermal Resistance-Junction to Ambient <sup>(Note 1)</sup>	R <sub>θJA</sub>	t≤10s	90
		Steady-State	110

## Electrical characteristics per line @25°C ( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	20		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=16V, V_{GS}=0V$	-	-	1	$\mu A$
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 8V$	-	-	$\pm 10$	$\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.75	1	V
Drain-Source On-state Resistance <sup>(Note 2)</sup>	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=4.5A$		36	45	m $\Omega$
		$V_{GS}=2.5V, I_D=3.5A$		45	60	
		$V_{GS}=1.8V, I_D=2A$		56	85	
Diode Forward Voltage <sup>(Note 2)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=1A$		0.7	1.3	V
<b>Gate Charge Characteristics</b> (Note 3)						
Total Gate Charge	Qg	$V_{GS}=4.5V, V_{DS}=10V,$ $I_D=4.5A$		3		nC
Gate-Source Charge	Qgs			0.6		
Gate-Drain Charge	Qgd			1		
<b>Dynamic Characteristics</b> (Note 3)						
Gate Resistance	$R_G$	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		3.3		$\Omega$
Input Capacitance	$C_{ISS}$	$V_{GS}=0V, V_{DS}=10V,$ $f=1MHz$		240		pF
Output Capacitance	$C_{OSS}$			46		pF
Reverse Transfer Capacitance	$C_{RSS}$			27		pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=10V, R_G=6\Omega, I_{DS}=1A$ $V_{GS}=10V, R_L=10\Omega$		2.5	4.5	ns
Turn-Off Delay Time	$t_{d(off)}$			13.5	24.5	ns
Turn-On Rise Time	$t_r$			13	23.5	ns
Turn-On Fall Time	$t_f$			2.5	4.5	ns
Reverse Recovery Time	$t_{rr}$	$I_{SD}=4.5A, di_{SD}/dt=100A/us$		7.2		ns
Reverse Recovery Charge	Qrr	$I_{SD}=4.5A, di_{SD}/dt=100A/us$		2.2		nC

## Note:

1. Surface Mounted on 1in<sup>2</sup> pad area,  $t_s \leq 10sec$ .
2. Pulse test ; pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
3. Guaranteed by design, not subject to production testing.

Typical Characteristics

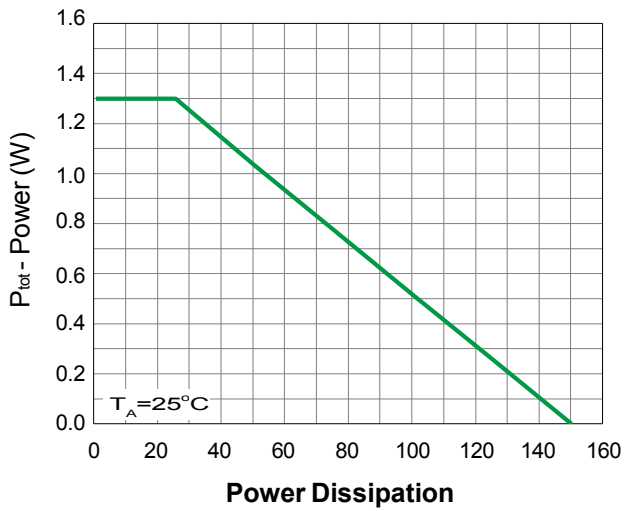


Fig 1.  $T_j$ - Junction Temperature ( $^\circ C$ )

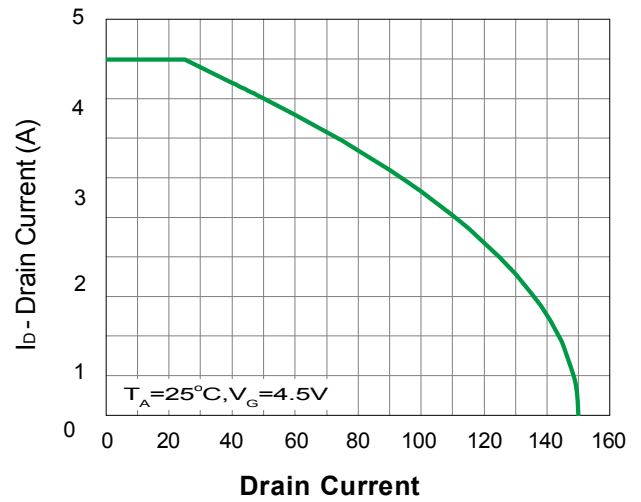


Fig 2.  $T_j$ - Junction Temperature ( $^\circ C$ )

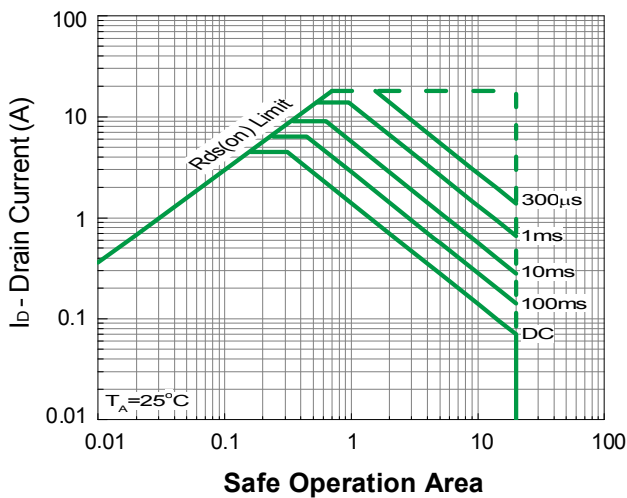


Fig 3.  $V_{DS}$  - Drain - Source Voltage (V)

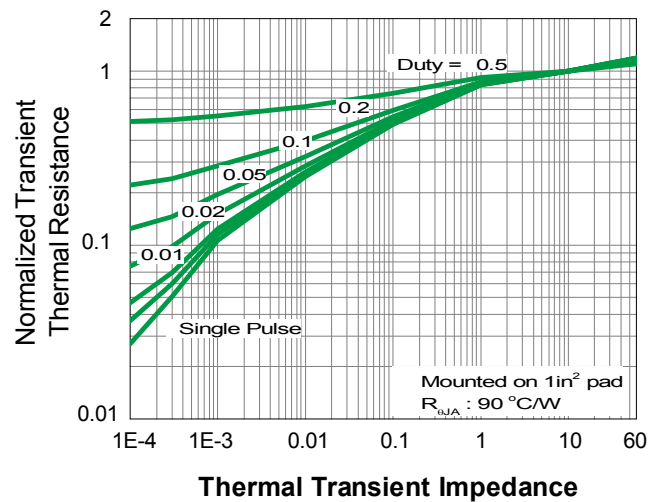


Fig 4. Square Wave Pulse Duration (sec)

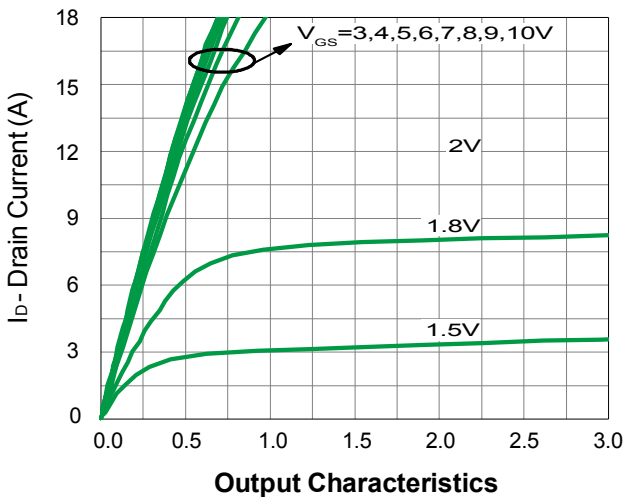


Fig 5.  $V_{DS}$  - Drain-Source Voltage (V)

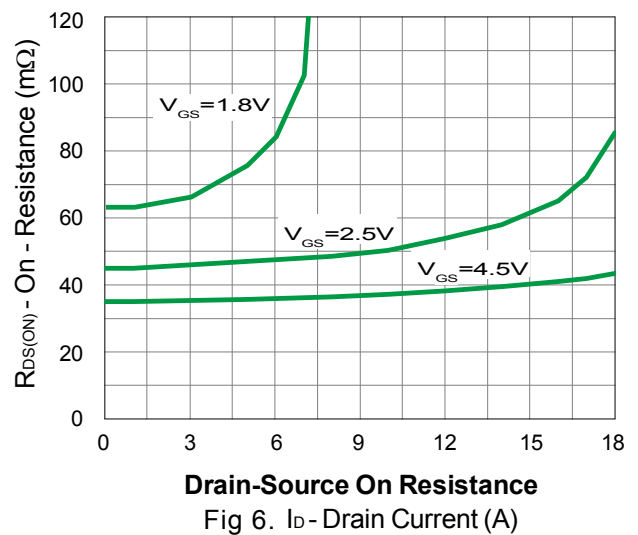
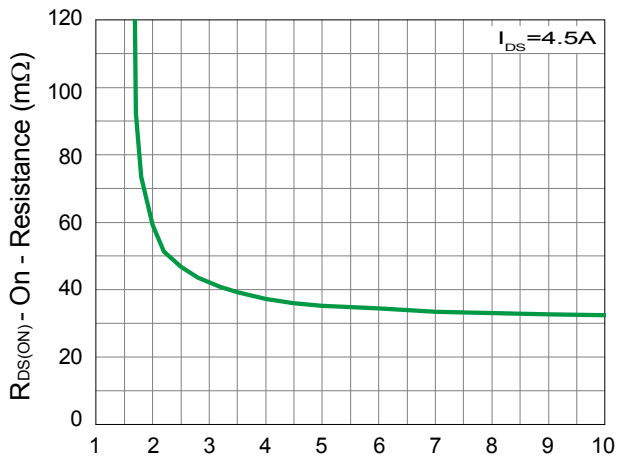
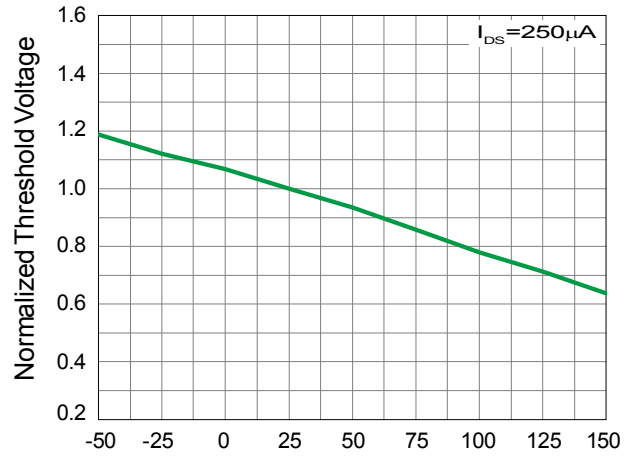


Fig 6.  $I_D$  - Drain Current (A)



Gate-Source On Resistance

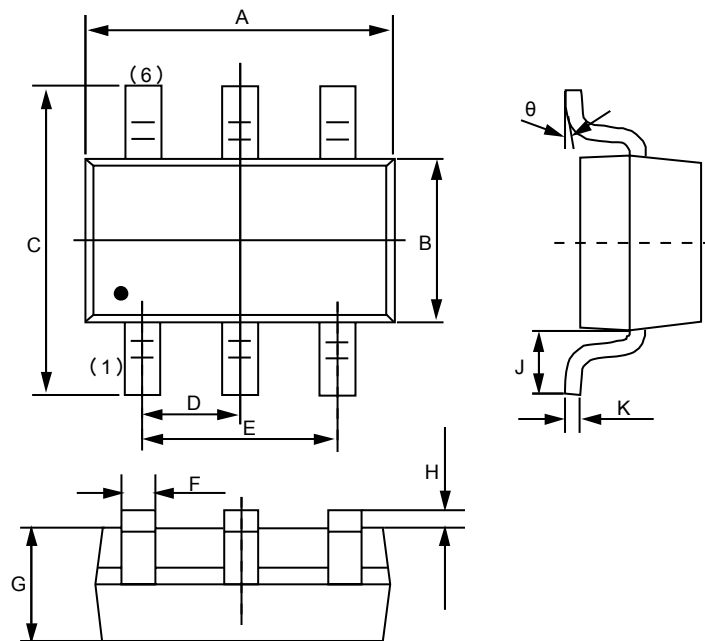
Fig 7.  $V_{GS}$  - Gate - Source Voltage (V)



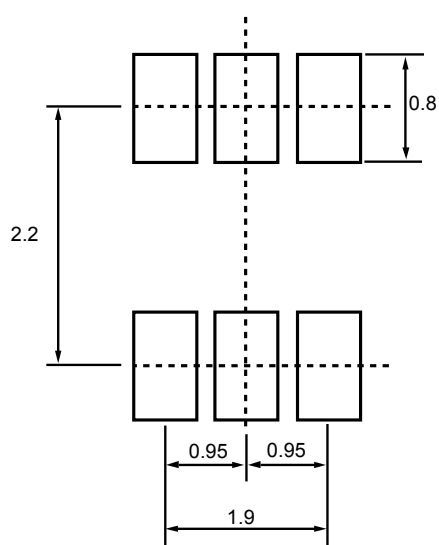
Gate Threshold Voltage

Fig 8.  $T_j$  - Junction Temperature (°C)

Product dimension (SOT-23-6L)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.820	3.020	0.111	0.119
B	1.500	1.700	0.059	0.067
C	2.650	2.950	0.104	0.116
D	0.950 (BSC)		0.037 (BSC)	
E	1.800	2.000	0.071	0.079
F	0.300	0.500	0.012	0.020
G	1.050	1.150	0.041	0.045
H	0.000	0.100	0.000	0.004
J	0.45	0.60	0.0180	0.0236
K	0.100	0.200	0.004	0.008
$\theta$	0°	8°	0°	8°




Unit:mm

## Ordering information

Device	Package	Shipping
PDNM6T20V2E	SOT-23-6L (Pb-Free)	3000 / Tape & Reel


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